

United States Patent Application Serial No. 09/551,018  
Attorney Docket No. 478

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re United States Patent Application of:

Applicants: Chongying Xu, et al.

Serial No: 09/551,018

Date Filed: April 18, 2000

Title: Silicon Reagents and Low Temperature CVD  
Method of Forming Silicon-Containing Gate  
Dielectric Materials Using Same

Group Art Unit: 1714

Examiner: Cephia D. Toomer

Confirmation No.: 2050

Customer No.: 25559

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September 22, 2003  
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**AMENDMENT RESPONDING TO JULY 11, 2003 FINAL OFFICE ACTION IN U.S.  
PATENT APPLICATION NO. 09/551,018 AND  
REQUEST FOR CONTINUED EXAMINATION UNDER 35 U.S.C. § 132**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated July 11, 2003, Applicant respectfully requests entry of the following Amendments and consideration of the subsequent remarks.